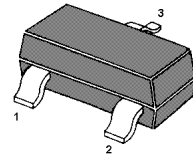


BF821

PNP Silicon High Voltage Transistors

for high voltage switching and amplifier applications.



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	300	V
Collector Emitter Voltage	$-V_{CEO}$	300	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	50	mA
Peak Collector Current	$-I_{CM}$	100	mA
Peak Base Current	$-I_{BM}$	50	mA
Total Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 20\text{ V}$, $-I_C = 25\text{ mA}$	h_{FE}	50	-	-
Collector Base Cutoff Current at $-V_{CB} = 200\text{ V}$	$-I_{CBO}$	-	10	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	300	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	300	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C = 30\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	0.8	V
Current Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$, $-I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	60	-	MHz
Collector Output Capacitance at $-V_{CB} = 20\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	6	pF

